



Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known	
			Application Number	10/642,305
			Filing Date	08/18/2003
			First Named Inventor	Hongyong ZHANG et al.
			Art Unit	2811
			Examiner Name	Douglas Owens
Sheet	1	of	Attorney Docket Number	740756-2646

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ² (if known)				
DWO		JP 62-104117 A	05/14/1987	YUKI		FULL

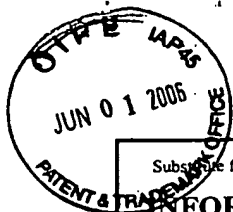
OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature	/Douglas W Owens/	Date Considered	07/10/2006
-----------------------	-------------------	--------------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.



Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			Complete if Known		
			Application Number	10/642,305	
			Filing Date	08/18/2003	
			First Named Inventor	Hongyong ZHANG et al.	
			Art Unit	2811	
			Examiner Name	Douglas Owens	
			Attorney Docket Number	740756-2646	
Sheet	1	of	3		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
DWO		US-4,059,461	11/22/1977	Fan et al.	
DWO		US-4,229,502	10/21/1980	Wu et al.	
DWO		US-4,309,225	01/05/1982	Fan et al.	
DWO		US-4,785,962	11/22/1988	Toshima	
DWO		US-4,814,292	03/21/1989	Sasaki et al.	
DWO		US-4,951,601	08/28/1990	Maydan et al.	
DWO		US-5,108,843	04/28/1992	Ohtaka et al.	
DWO		US-			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ Number ⁴ Kind Code ⁵ (if known)				
DWO		JP 01-268064 A	10/25/1989	Hashimoto et al.		FULL
DWO		JP 60-105216	06/10/1985	Shimizu et al.		FULL

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁷
DWO		Mimura et al., "High Performance Low-Temperature Poly-Si n-Channel TFT's for LCD," <u>IEEE Transactions on Electron Devices</u> , Vol. 36, No. 2, pp. 351-359 (Feb. 1989)	
DWO		Ohwada, et al., "Peripheral Circuit Integrated Poly-Si TFT LCD with Gray Scale Representation", <u>IEEE Transactions on Electron Devices</u> , Vol. 36, No. 9, pp. 1923-1928 (Sept. 1989)	
DWO		Masumo et al., "Low Temperature Fabrication of Poly-Si TFT by Laser Induced Crystallization of a-Si," <u>Journal of Non-Crystalline Solids</u> , Vol. 115, pp. 147-149 (1989)	
DWO		Wright et al., "The Effect of Fluorine in Silicon Dioxide Gate Dielectrics," <u>IEEE Transactions on Electron Devices</u> , Vol. 36, No. 5, pp. 879-889 (May 1989)	

Examiner Signature	/Douglas W Owens/	Date Considered	07/10/2006
--------------------	-------------------	-----------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	10/642,305
				Filing Date	08/18/2003
				First Named Inventor	Hongyong ZHANG et al.
				Art Unit	2811
Examiner Name	Douglas Owens				
Sheet	2	of	3	Attorney Docket Number	740756-2646

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
	DWO	Wright et al., "Hot-Electron Immunity of SiO ₂ Dielectrics with Fluorine Incorporation", <u>IEEE Electron Device Letters</u> , Vol. 10, No. 8, pp. 347-348 (Aug. 1989)		
		Young & Gill, "Mobile Ion Instabilities in Polycrystalline Silicon Thin Film Transistors", <u>Applied Surface Science</u> , Vol. 39, pp. 364-367 (1989)		
		Serikawa et al., "Low-Temperature Fabrication of High-Mobility Poly-Si TFT's for Large-Area LCD's", <u>IEEE Transactions on Electron Devices</u> , Vol. 36, No. 9, pp. 1929-1933 (Sept. 1989)		
		Malhi et al., "Characteristics and Three-Dimensional Integration of MOSFET's in Small-Grain LPCVD Polycrystalline Silicon", <u>IEEE Transactions on Electron Devices</u> , Vol. ED-32, No. 2, pp. 258-281 (Feb. 1985)		
		Aritome et al., "Low-temperature nitridation of fluorinated silicon dioxide films in ammonia gas", <u>Applied Physics Letters</u> , Vol. 51, No. 13, pp. 981-983 (Sept. 28, 1987)		
		Zaima et al., "Effects of fluorine ion implantation on metal-oxide-semiconductor devices of silicon-on-sapphire", <u>Applied Physics Letters</u> , Vol. 52, No. 6, pp. 459-461 (Feb. 8, 1988)		
		Georgiev, "Electrophysical Properties of Plasma SiO ₂ Prepared from SiCl ₄ and N ₂ O", <u>Bulgarian Journal of Physics</u> , Vol. 12, No. 5, pp. 501-506 (1985)		
		Perchard et al., "Characterization of a multiple-step in-situ plasma enhanced chemical vapor deposition (PECVD) tetraethylorthosilicate (TEOS) planarization scheme for submicron manufacturing", <u>SPIE</u> , Vol. 1188, Multichamber and In-Situ Processing of Electronic, pp. 75-85 (1989)		
		Parks et al., "The Chemical Interface of Microwave Plasma Deposited SiO ₂ Films", <u>Materials Research Society</u> , Vol. 105, pp. 133-138 (1988)		
	↓	Liu et al., "Raman Characterisation of stress in Recrystallised Silicon-On Insulator", <u>Electronics Letters</u> , Vol. 24, No. 23, pp. 1420-1422 (Nov. 10, 1988)		
	DWO	Veprek et al., "Effect of Grain Boundaries on the Raman Spectra, Optical Absorption, and Elastic Light Scattering in Nanometer-Sized Crystalline Silicon", <u>Physical Review B</u> , Vol. 36, pp. 3344-3350 (Aug. 1987)		

Examiner Signature	/Douglas W Owens/	Date Considered	07/10/2006
--------------------	-------------------	-----------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	10/642,305
				Filing Date	08/18/2003
				First Named Inventor	Hongyong ZHANG et al.
				Art Unit	2811
				Examiner Name	Douglas Owens
Sheet	3	Of	3	Attorney Docket Number	740756-2646

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
	DWO	Takenaka et al., "High Mobility Poly-Si Thin Film Transistors Using Solid Phase Crystallized a-Si Films Deposited by Plasma-Enhanced Chemical Vapor Deposition, <u>Japanese J. of Applied Physics</u> , Vol. 29, No. 12, pp. L2380-L2383(Dec. 1990)		
	DWO	Sameshima et al., "XeCl Excimer Laser Annealing Used to Fabricate Poly-Si TFT's", <u>Japanese J. of Applied Physics</u> , Vol. 28, No. 10, pp. 1789-1793 (Oct. 1989)		
	DWO	Madan et al., "Use of PECVD System in Thin Film Technology", <u>Workshop on Industrial Plasma Applications</u> , pp. 1-11 (Sept. 1989)		
	DWO	Lucovsky et al., "Formation of Silicon-Based Hetrostructures in Multichamber Integrated-Processing Thin-Film Deposition System", <u>Multichamber and In-Situ Processing of Electronic Materials</u> , Vol. 1188, pp. 140-150 (1989)		
	DWO	Sameshima et al., "XeCl Excimer Annealing Used in the Fabrication of Poly-Si TFT's", <u>IEEE Electron Device Letters</u> , Vol. EDL-7, No. 5, pp. 276-278 (May 1986)		
	DWO	Sera et al., "High Performance TFT's Fabricated by XeCl Excimer Laser Annealing of Hydrogenated Amorphous-Silicon Film, <u>IEEE Transactions on Electron Devices</u> , Vol. 36, No. 12, pp. 2868-2872 (Dec. 1989)		
	DWO	S. Wolf & R.N. Tauber, <u>Silicon Processing for the VLSI Era-Process Technology</u> , pp. 164-175 (1986)		
		U.S. Patent Application No. 06/944,803, Mayden et al., filed December 19, 1986 (Abandoned)(Parent of U.S. Patent No. 4,951,601)		

Examiner Signature	/Douglas W Owens/	Date Considered	07/10/2006
--------------------	-------------------	-----------------	------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.